

Tristan Demming

# ECE 310 – Microelectronics I

## Homework #5

Fall 2021

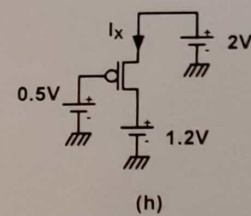
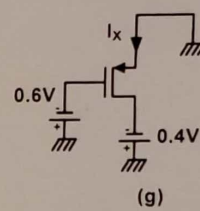
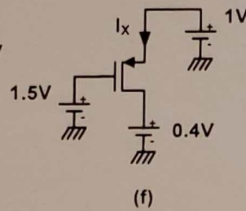
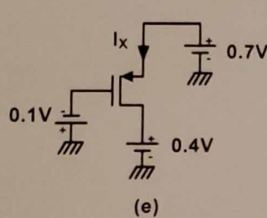
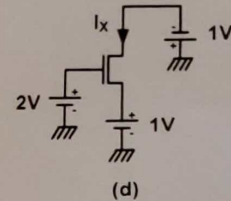
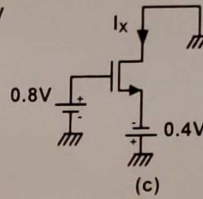
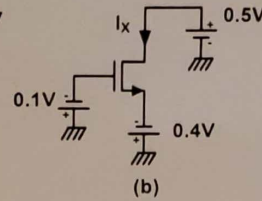
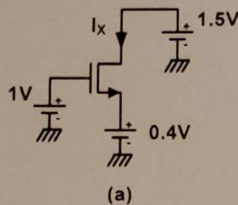
Dr. Suat Ay

(Due Date: 10/25/2021, 8.30am, Monday)

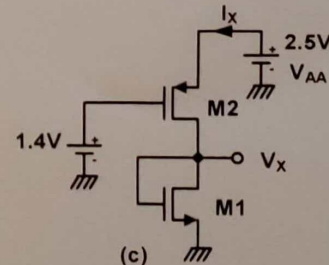
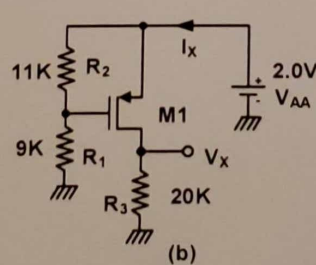
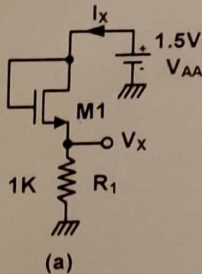
For the problems below, use;

$KP_n = 100 \mu A/V^2$ ,  $V_{THn} = +0.5V$  for NMOS, and  $KP_p = 50 \mu A/V^2$ ,  $V_{THp} = -0.4V$  for PMOS transistors.

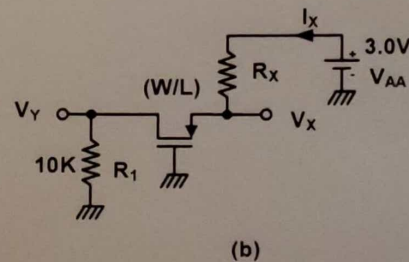
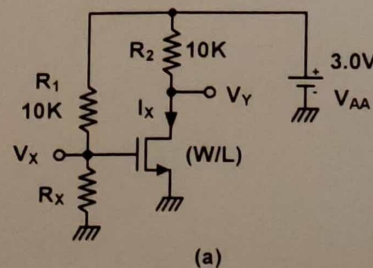
1. (40 points) Find the operating conditions (ON/OFF, LIN/SAT) and biasing conditions ( $V_{OD}$ ,  $V_{DSAT}$ ,  $I_X$ ) of the following transistors. Use  $(W/L)_n = 10$  and  $(W/L)_p = 5$ .



2. (30 points) Find the operating conditions (ON/OFF, LIN/SAT) and unknown voltage and current values ( $V_X$ ,  $I_X$ ) of the following transistors and circuits. Use  $(W/L)_n = 10$  and  $(W/L)_p = 5$ .



3. (30 points) Find unknown parameters ( $V_X$ ,  $I_X$ ,  $V_Y$ ,  $W/L$ ) of the following circuits by biasing NMOS transistor 0.3V in ON and 0.5V in SAT region while PMOS transistor 0.8V in ON and 0.5V in SAT region.



## Tristan Denning Problem 1(a.)

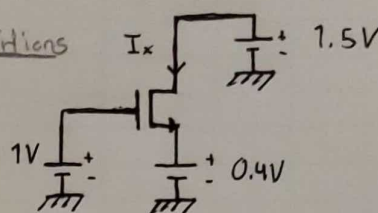
HW # 05

1(a)

1 Situation: Find the operating conditions (ON/OFF, LIN/SAT) and biasing conditions ( $V_{DD}$ ,  $V_{DSAT}$ ,  $I_x$ ) of the following transistors.

Given Values:  $(\frac{W}{L})_n = 10$ ,  $(\frac{W}{L})_p = 5$ ,

$KP_n = 100 \mu A/V^2$ ,  $V_{THn} = +0.5V$ ,  $KP_p = 50 \mu A/V^2$ ,  $V_{THp} = -0.4V$   
For parts (a)-(h).

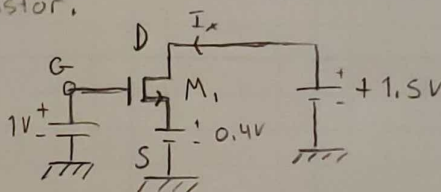


2 Goal: To determine the biasing conditions and operating conditions as defined in the problem statement for the given transistor.

3 Plan: To utilize known relationships for  $V_{DD}$ ,  $V_{D,sat}$ ,  $V_{THn}$ ,  $V_{THp}$ ,  $I_{SD}$ ,  $I_{OS}$ ,  $V_{GS}$ ,  $V_{SP}$ ,  $V_{DS}$  ... etc... to determine the biasing conditions and operating conditions for the given transistor.

4 Solution:

Redraw



Observe: NMOS transistor

$$\therefore V_D > V_S \\ 1.5 > 0.4$$

$$V_D = 1.5V$$

$$V_G = 1.0V$$

$$V_S = 0.4V$$

$$(ON/OFF) \quad V_{GS} = 1.0 - 0.4 \\ = 0.6V$$

$$V_{GS} > V_{THn} \\ 0.6V > 0.5V$$

$\therefore M_1$  is ON

(SAT/LIN,  $V_{DD}$ )

$$V_{DD} = V_{GS} - V_{TH} \\ = 0.6 - 0.5 \\ = 0.1V$$

$$\therefore V_{DD} = 0.1V$$

$$V_{DS} = 1.5 - 0.4 \\ = 1.1V$$

$$V_{DS} > V_{DD} \\ 1.1V > 0.1$$

$\therefore M_1$  is SAT

1(a) (continued)

(V<sub>O,SAT</sub>)  $V_{O,SAT} = V_{DS} - V_{DD}$   
 $= 1.1V - 0.1V$

$V_{O,SAT} = 1.0V$

(I<sub>x</sub>)

$$I_x = \frac{1}{2} K P_n \left( \frac{W}{L} \right)_n (V_{DS})^2$$
$$= 0.5 (100 \times 10^{-6}) (10) (0.1)^2$$

$I_x = 5 \mu A$

5 Sanity Check:

Unit analysis, I<sub>x</sub>

$$I_x [A] = \left[ \frac{A \times 10^{-6}}{V^2} \right] \cdot [-] \cdot [V^2]$$

$$[A] = [A]$$

\* Answer is in correct units, and in appropriate magnitude,  $[\mu A]$



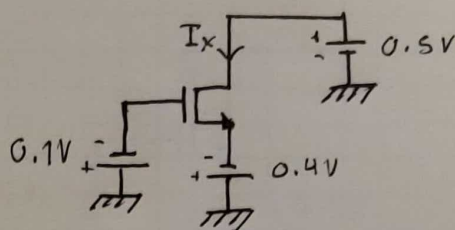
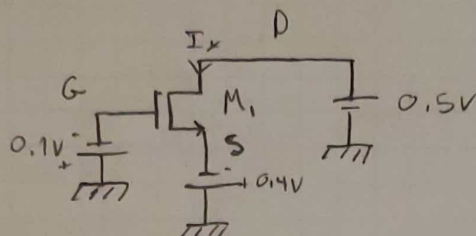
1(b.) Situation: (See 1(a).)

2 Goal: (See 1(a).)

3 Plan: (See 1(a).)

4 Solution:

Redraw:



Observe: NMOS Transistor with  $V_D > V_S$ ,  $0.5 > -0.4$

$$V_D = 0.5V$$

$$V_S = -0.4V$$

$$V_G = -0.1V$$

(ON/OFF)

$$V_{GS} = V_G - V_S = -0.1 - (-0.4)$$

$$V_{GS} = -0.3V$$

$$V_{GS} < V_{TH}$$

$$-0.3 < 0.5V$$

$\therefore M_1$  is OFF

$$\therefore V_{DD} = V_{DSAT} = I_x = \phi$$

$\therefore$  Neither LIN NOR SAT

5 Sanity Check

Reasonable Result From Straightforward Process.

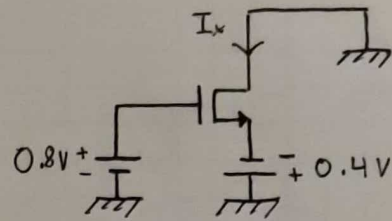
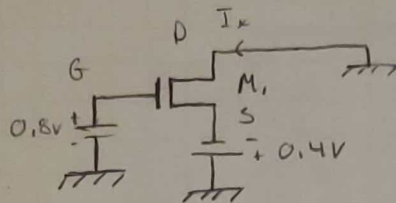
1(c.) 1 Situation: (see 1(a))

2 Goal: (see 1(a))

3 Plan: (see 1(a))

4 Solution:

Redraw:



Observe:

NMOS Transistor

$$V_D = 0$$

$$V_G = 0.8$$

$$V_S = -0.4$$

$$V_{DS} = 0.4V$$

(ON/OFF)

$$V_{GS} = 0.8 - (-0.4) = 1.2V$$

$$V_{GS} > V_{TH,n}$$

$$1.2 > 0.5$$

$\therefore M_1, ON$

(SAT/LIN,  $V_{DD}$ )

$$V_{DD} = V_{GS} - V_{TH}$$

$$= 1.2 - 0.5$$

$$\therefore V_{DD} = 0.7V$$

$$V_{DS} \leq V_{DD}$$

$$0.4 \leq 0.7V$$

$\therefore M_1$  is in LIN mode

$$\therefore V_{D,SAT} = \phi$$

$$(I_x) \text{ LIN Region: } I_x = \frac{1}{2} k_p n \left(\frac{W}{L}\right)_n (2(V_{DD})(V_{DS}) - V_{DS}^2)$$

$$= 0.5 (100 \times 10^{-6}) (10) (2(0.7)(0.4) - (0.4)^2)$$

$$I_x = 200 \mu A$$

5 Sanity Check:

Reasonable result from straightforward Process.

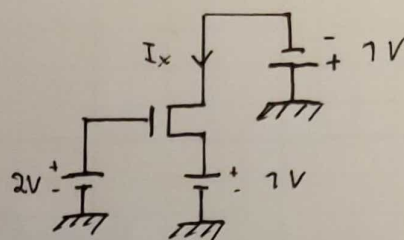
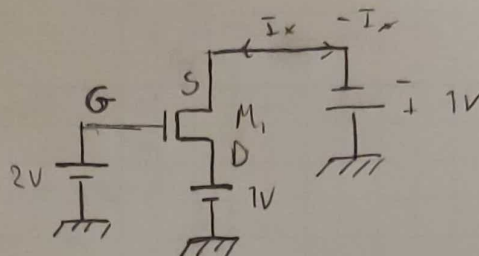
1(d.) Situation: (See 1(a.))

2 Goal: (See 1(a.))

3 Plan: (See 1(a.))

4 Solution:

Redraw:



Observe: Not defined as NMOS or PMOS

Let  $I_x$  be a negative current, so current flows from D to S as labeled  
 $(-I_x) = I_{DS}$

$$V_D = 1V$$

$$V_S = -1V$$

$$V_G = 2V$$

Then  $M_1$  is NMOS

(ON/OFF)

$$V_D > V_S; 1V > -1V$$

$$V_{GS} = 2V + 1V = 3V$$

$$V_{GS} > V_{TH,n}$$

$$3V > 0.5V$$

$$\therefore M_1 \text{ ON}$$

(SAT/LIN,  $V_{DS}$ )

$$V_{GS} - V_{TH} = V_{DS}$$

$$3 - 0.5 = 2.5V; V_{DS} = 2.5V$$

$$V_{DS} < V_{DS,sat}$$

$$1 - (-1)V < 2.5V$$

$$2V < 2.5V$$

$$\therefore M_1 \text{ in LIN Region}$$

$$\therefore V_{D,SAT} = \emptyset$$

( $I_x$ ) in linear

$$\begin{aligned} -I_x = I_{DS} &= \frac{1}{2} k_p \left( \frac{W}{L} \right)_n (2(V_{GS} - V_{TH}) - V_{DS}) V_{DS} \\ &= 0.5(100)(10) (2(2.5)(2) - (2)^2) \times 10^{-6} \end{aligned}$$

$$\therefore \begin{aligned} I_{DS} &= 3 \text{ mA} \\ I_x &= -3 \text{ mA} \end{aligned}$$

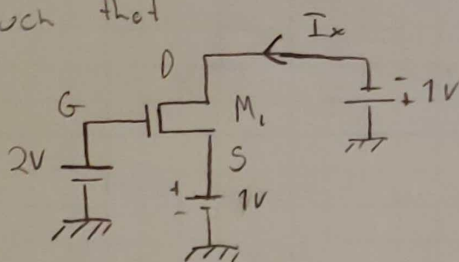


1(d) (continued)

Sanity Check:

Under the assumption that  $M_1$  was an NMOS Transistor, the result seems reasonable

If I chose the S and D to be switched such that



And  $M_1$  is NMOS, this is incorrect, since  $V_D < V_S$

I could have instead chosen the same configuration as above, but assumed  $M_1$  is PMOS.

Then  $I_x$  would be negative, flowing from S to D, (ISO)

In which case: ( $M_1$  is PMOS)

$$V_{SG} = 1 - 2 = -1V$$

$$V_{THP} = -0.4V$$

$$V_{SG} \stackrel{?}{>} |V_{THP}|$$

$$-1V < 0.4V, \text{ so } M_1 \text{ would be OFF}$$

and All other parameters  $\emptyset$

$\therefore$  So the assumption that  $M_1$  is NMOS with  $I_x$  being negative and the subsequent results seem reasonable

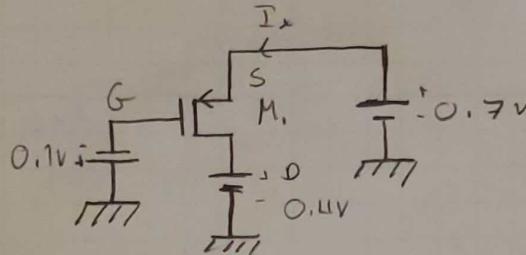
1(e.) Situation: (See 1(a.))

1 Goal: (See 1(a.))

2 Plan: (See 1(a.))

3 Solution:

Redraw:



Observe:

PMOS Transistor with  $V_s > V_o$

$$V_s = 0.7 \text{ V}$$

$$V_o = 0.4 \text{ V}$$

$$V_g = -0.1 \text{ V}$$

(ON/OFF)

$$V_{sg} = 0.7 - (-0.1) \\ = 0.8 \text{ V}$$

$$V_{sg} > |V_{THP}|$$

$$0.8 \text{ V} > 0.4 \text{ V}$$

$\therefore M_1, \text{ ON}$

(SAT/LIN,  $V_{oo}$ )

$$V_{so} = 0.7 - 0.4 \\ = 0.3 \text{ V}$$

$$V_{oo} = V_{sg} - |V_{TH}| \\ = 0.8 - 0.4 \\ = 0.4 \text{ V}$$

$$V_{oo} = 0.4 \text{ V}$$

$$V_{so} < V_{oo} \\ 0.3 \text{ V} < 0.4 \text{ V} \quad \therefore$$

$M_1$  is in LIN Reg.

$$V_{o, \text{SAT}} = \phi$$

$\therefore M_1$  is Not saturated

( $I_x$ ) Linear Mode

$$I_{so} = I_x = \frac{1}{2} \mu_p \left( \frac{W}{L} \right)_p (2(V_{oo})(V_{so}) - V_{so}^2) \\ = 0.5 (500 \times 10^{-6}) (5) (2(0.4)(0.3) - (0.3)^2)$$

$$I_x = 188 \text{ nA}$$

Sanity Check:

Reasonable result from straight forward process.



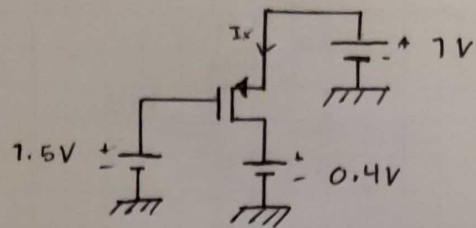
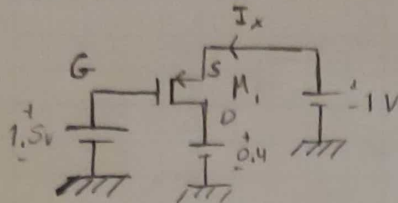
1(f.) Situation: (See 1(a))

2 Goal: (See 1(a))

3 Plan: (See 1(a))

4 Solution:

Redraw:



Observe: PMOS Transistor, with  $V_s > V_D$

$$V_G = 1V$$

$$V_G = 1.5V$$

$$V_D = 0.4V$$

(ON/OFF)

$$V_{SG} = 1 - 1.5V$$

$$= -0.5V$$

$$V_{SG} < |V_{THP}|$$

$$-0.5V < 0.4V$$

$\therefore M_1$  is OFF

$\therefore M_1$  is neither SAT nor LIN

$\therefore V_{D,SAT}, V_{DD}, I_x = \emptyset$

5 Sanity Check:

Answer is reasonable and came from a straightforward process.

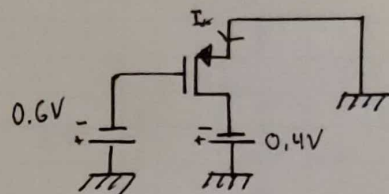
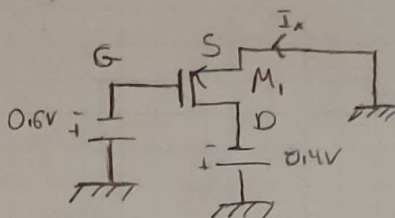
1(b)

1. Situation (See 1(a.))

2 Goal: (See 1(a.))

3 Plan: (See 1(a.))

4 Solution:

Redraw:

Observe:

$$V_S = 0V \quad \therefore \text{GND}$$

$$V_G = -0.6V$$

$$V_D = -0.4V$$

(ON/OFF)

$$V_{SG} = 0 + 0.6V \\ = +0.6V$$

$$V_{SG} > |V_{TH,p}| \\ 0.6V > 0.4V$$

 $\therefore M_1 \text{ ON}$ (SAT/LIN,  $V_{DD}$ )

$$V_{SD} = 0 - (-0.4V) \\ = 0.4V$$

$$V_{DD} = V_{SG} - |V_{TH,p}| ; V_{DD} = 0.2V \\ = 0.6 - 0.4 \\ = 0.2V$$

$$V_{SD} > V_{DD} \\ 0.4 > 0.2$$

 $\therefore M_1 \text{ is SAT}$ 

$$V_{O,SAT} = V_{SD} - V_{DD}$$

$$= 0.4 - 0.2$$

$$= 0.2V$$

$$\therefore V_{O,SAT} = 0.2V$$

(I<sub>x</sub>) SAT region

$$I_x = \frac{1}{2} K_P \left(\frac{W}{L}\right)_p V_{DD}^2$$

$$= 0.5(50 \times 10^{-6})(5)(0.2^2)$$

$$I_x = 5 \mu A$$

5 Sanity Check:

Answer is reasonable and on the same order of magnitude as results from similar problems

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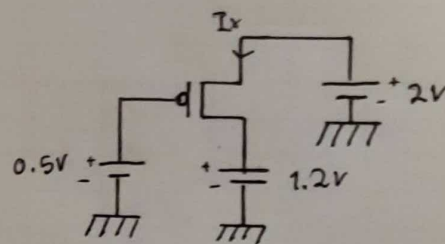
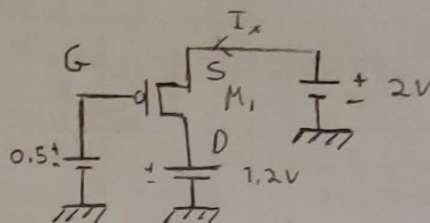
1(h.) Situation: (See 1(a))

2 Goal: (See 1(a))

3 Plan: (See 1(a))

4 Solution:

Redraw:



Observe: PMOS Transistor

$$V_G = 0.5V$$

$$V_S = 2V$$

$$V_D = 1.2V$$

(ON/OFF)

$$V_{SG} = 2 - 0.5$$

$$= 1.5V$$

$$V_{SG} > |V_{TH,p}|$$

$$1.5V > 0.4V$$

∴  $M_1$  ON

(SAT/LIN)

$$V_{SD} = 2 - 1.2$$

$$= 0.8V$$

$$V_{OD} = V_{SG} - |V_{TH}|$$

$$= 1.5 - 0.4$$

$$= 1.1V$$

∴  $V_{OD} = 1.1V$

$$V_{SD} < V_{OD}$$

$$0.8 < 1.1$$

∴  $M_1$  is in LIN Region

∴  $V_{O,SAT} = \emptyset$

( $I_x$ ) Linear Reg

$$I_x = \frac{1}{2} k_{PP} \left(\frac{W}{L}\right)_p (2(V_{OD})(V_{SD}) - (V_{SD})^2)$$

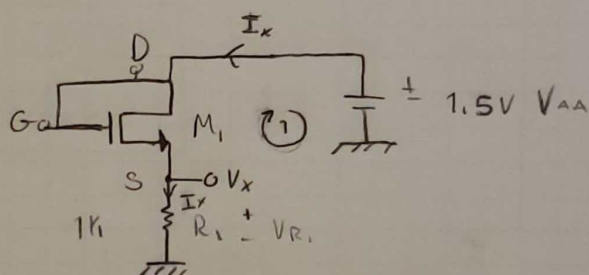
$$= \frac{1}{2} 50 \times 10^{-6} (5) (2(1.1)(0.8) - (0.8)^2)$$

$I_x = 140 \mu A$

5 Sanity Check

Result is reasonable and came from a straightforward process



**2(a)**1 Situation: Find the operatingConditions (ON/OFF, LIN/SAT) and Voltage and Current values ( $V_x$  and  $I_x$ ) for the following transistors. (a-c)Use:  $(\frac{W}{L})_n = 10$ ,  $(\frac{W}{L})_p = 5$ ,  $KP_n = 100 \mu A/V^2$  $V_{THn} = 0.5V$ ,  $KP_p = 50 \mu A/V^2$ ,  $V_{THp} = -0.4V$ 2 Goal: To determine the biasing conditions and operating conditions as defined in the problem statement for each corresponding transistor in parts 2(a) - 2(c).3 Plan: To utilize known relationships and equations for  $V_{DD}$ ,  $V_{DSAT}$ ,  $V_{TH}$ ,  $I_{SD}$ ,  $I_{OS}$ ,  $V_{GS}$  ... etc. to determine the operating and biasing conditions for each transistor4 Solution:Redraw:

Observe:

NMOS Transistor

$$V_D = V_{DD} = 1.5V = V_G$$

$$V_x = V_S$$

$$\therefore V_{GS} = V_{DS} = 1.5 - V_x$$

(SAT/LIN)

$$V_{DS} > V_{GS} - V_{TH}$$

$$V_{DS} > V_{GS} - 0.5$$

$$0 > -0.5$$

$$\therefore M_1 \text{ is ON and SAT. always.}$$
( $I_x$ ) SAT

$$I_x = \frac{1}{2} KP_n \left(\frac{W}{L}\right)_n (V_{GS} - V_{TH})^2$$

KVL @

$$V_{GS} = 1.5 - 1000 I_x$$

 $\therefore$  Ohm's law  $R_1$ 

$$\therefore I_x = 0.5(100 \times 10^{-6})(10)(1.5 - 1000 I_x - 0.5)^2 \quad (1)$$

**2(w)** (continued)

Solving equation (1) for  $I_x$  yields

$$I_x = 268 \mu\text{A} \quad \text{or} \quad I_x = 3.732 \text{ mA}$$

Then  $V_x = 1000 I_x$

$$\therefore V_x = 0.268 \text{ V}, \text{ or } V_x = 3.732 \text{ V}$$

To fulfill  $V_D > V_S$ ,  $1.5 \text{ V} > V_S$ ,

$$\boxed{V_x = 0.268 \text{ V}} \quad \text{must be true}$$

$$\therefore \boxed{I_x = 268 \mu\text{A}}$$

Sanity Check

$$\begin{aligned} I_x &= \frac{1}{2} \mu P_n \left(\frac{W}{L}\right)_N (V_{GS} - V_{TH})^2 \\ &= 0.0005 ((1.5 - 0.268) - 0.5)^2 \\ &= 268 \mu\text{A} \end{aligned}$$

$\therefore$  Plugging  $V_x$  into  $I_x$  eqn yields the anticipated  $I_x$ .

Check ON/OFF  $V_{GS} > V_{TH}$

$$\begin{aligned} (1.5 - 0.268) &> 0.5 \\ 1.232 &> 0.5 \end{aligned}$$

✓

$M_1$  ON

Check SAT/LIN  $V_{DS} > V_{GS} - V_{TH}$

$$\begin{aligned} (1.5 - 0.268) &> (1.5 - 0.268) - 0.5 \\ 0 &> -0.5 \end{aligned}$$

✓

$M_1$  IS LIN

12/20

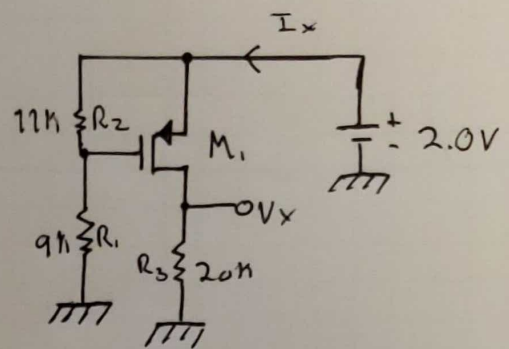
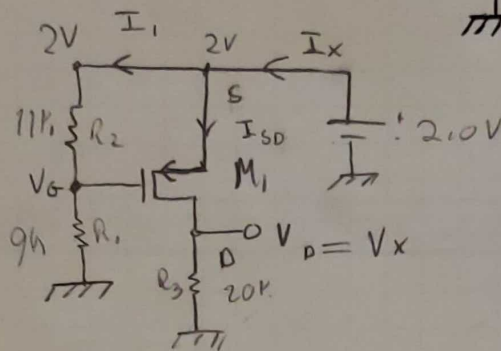
2(b)

situation: (See 2(a))

2 Goal: (See 2(a))

3 Plan: (See 2(a))

4 Solution:

Redraw:

Observe,

PMOS Transistor

$$V_D = V_X ; V_S = 2V$$

Find  $V_G$ Nodal Analysis at  $V_G$  Node,

$$\frac{2 - V_G}{11000} = \frac{V_G}{9000}$$

$$\therefore V_G = 0.9V$$

$$\therefore V_{SG} = 2 - 0.9 = 1.1V$$

(ON/OFF)

$$V_{SG} > |V_{THP}|$$

$$1.1V > 0.4V$$

$$\therefore \boxed{M_1 \text{ is ON}}$$

(SAT/LIN)

Assume Saturation, then verify

$$I_{SD} = \frac{1}{2} K_P \left( \frac{W}{L} \right)_P (V_{SG} - V_{TH})^2$$

$$= 0.000125 (1.1 - 0.4)^2$$

$$I_{SD} = 61.25 \mu A$$

$$\therefore V_X = V_D = 20000 (I_{SD})$$

$$= 1.225V$$

$$\therefore \boxed{V_X = 1.225V}$$



**2(b)** (Continued)

$$\therefore V_{SD} = 2 - 1.225 \\ = 0.775$$

Check  $V_{SD} > V_{SG} - |V_{THP}|$

$$0.775 > 1.1 - 0.4$$

$$0.775 > 0.7 \quad \checkmark$$

$\therefore$   **$M_1$  is indeed Saturated**

$$I_x = I_{SD} + I_1$$

$$= 61.25 \mu A + \frac{V_G}{9000}$$

$$= 61.25 \times 10^{-6} + 0.1 \times 10^{-3}$$

$$\therefore \boxed{I_x = 61.25 \mu A}$$

Sanity Check:

KVL Right Side:

$$2V - V_{SD} - V_D = 0$$

$$2V - 0.775V - 1.225V = 0$$

$$0 = 0 \quad \checkmark$$

KVL Left Side:

$$V_{R_1} + V_{SG} = 0.775 + 1.225$$

$$9000(0.1) + 11000(0.1) = 2$$

$$2V = 2V \quad \checkmark$$

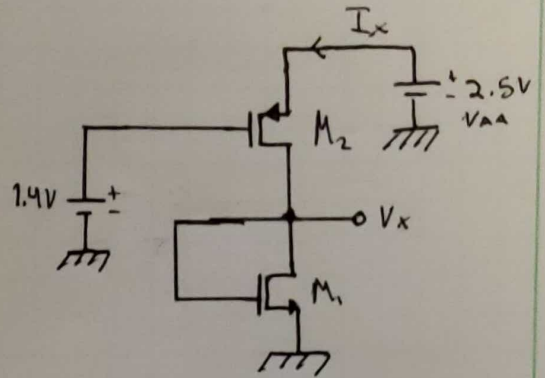
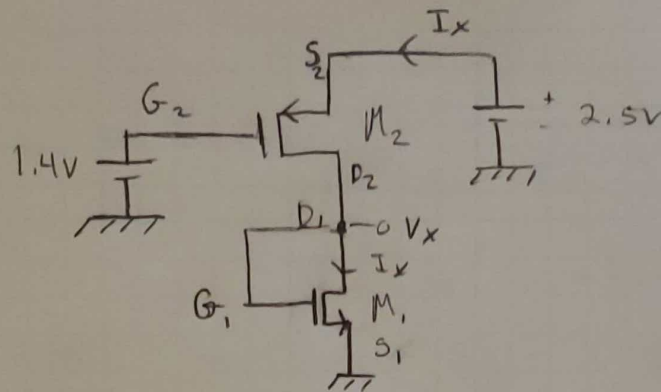
**2(c)** Situation: (See 2(a))

Goal: (See 2(a))

Plan: (See 2(a))

Solution:

Redraw:



Observe  $M_1$ , NMOS,  $M_2$ , PMOS

$$V_{G2} = 1.4, V_{S2} = 2.5V, V_{D2} = V_{D1}$$

$$V_{G1} = V_{D1}, V_{S1} = 0$$

$$I_x = I_{SD2} = I_{DS1}$$

$M_2$

(ON/OFF)

$$V_{SG} = 2.5 - 1.4 = 1.1V$$

$$V_{SG} > |V_{TH,P}|$$

$$1.1 > 0.4$$

$M_2$ , ON

$M_1$

(ON/OFF/SAT/LIN)

$$V_{GS} = V_{DS}$$

$$V_{DS} > V_{GS} - V_{TH,N}$$

$$V_{DS} - V_{GS} > -0.5V$$

$$0 > -0.5$$

$\therefore$   $M_1$  is SAT and ON

**2(c)** (Continued)Assume  $M_2$  is SAT

$$\begin{aligned}
 I_{SD} = I_x &= \frac{1}{2} k_{Pp} \left(\frac{W}{L}\right)_p (V_{SG} - |V_{TH}|)^2 \\
 &= 0.000125 (1.1 - 0.4)^2 \\
 &= 61 \mu A \quad \boxed{I_x = 61 \mu A} \quad \text{* through } M_1
 \end{aligned}$$

Then through  $M_1$ ,

$$\begin{aligned}
 I_{DS} &= \frac{1}{2} k_{Pn} \left(\frac{W}{L}\right)_n (V_{GS} - V_{TH})^2 \\
 61 \times 10^{-6} &= 0.0005 (V_{GS} - 0.5)^2 \\
 61 \times 10^{-6} &= 0.0005 (V_x - 0.5)^2
 \end{aligned}$$

$$\therefore V_x = 0.15V \quad \text{or} \quad 0.85V$$

For  $V_x = 0.15$ ,  $M_1$  cannot be on.

$$V_{GS} < V_{TH,n}$$

$$0.15 < 0.5$$

$$\therefore V_{GS} = V_x$$

$\therefore V_x$  must be ~~0.15~~  $0.85V$

$$\boxed{V_x = 0.85V}$$

Then  $M_2$  is SAT

$$\begin{aligned}
 \therefore V_{SD} &> V_{SG} - |V_{TH,p}| \\
 (2.5 - 0.85) &> (1.1 - 0.4) \\
 1.65 &> 0.7
 \end{aligned}$$

Sanity Check:

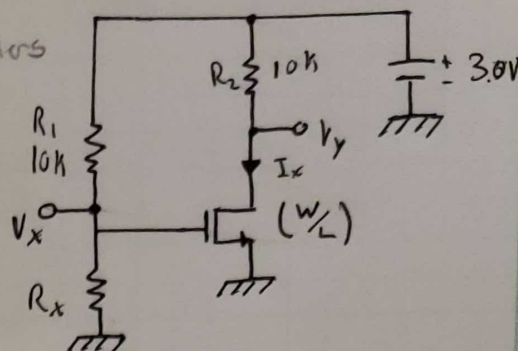
KVL Right Side:

$$\begin{aligned}
 2.5 - V_{SD} - V_x &= 0 \\
 2.5 - 1.65 - 0.85 &= 0 \\
 0 &= 0 \quad \checkmark
 \end{aligned}$$



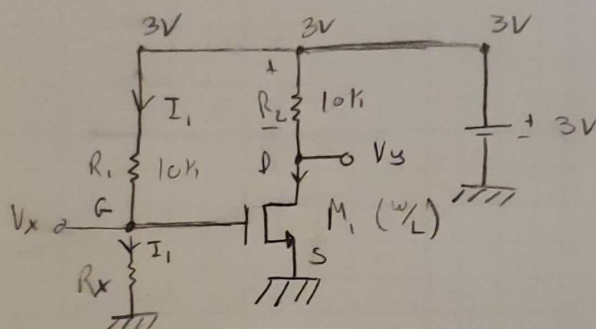
**3(a)**Situation: Find Unknown Parameters

$(V_x, I_x, V_y, w/L)$  of the following circuits by biasing NMOS Transistor  $0.3V$  in ON and  $0.5V$  in SAT while PMOS Transistor  $0.8V$  in ON and  $0.5$  in SAT region.



Goal: To Find the Unknown Parameters  $(V_x, I_x, V_y$  and  $w/L$ ).

Plan: To utilize known relationships for  $V_{DD}, V_{O,SAT}, V_{TH}, I_{D0}, I_{D0S}, V_G, V_S, V_D \dots$  etc, to Set up and solve expressions for  $(V_x, I_x, V_y$  and  $w/L$ )

4 Solution:RedrawObserve:

NMOS Transistor

$$V_S = 0$$

$$V_D = V_y$$

$$V_x = V_G$$

$$V_{GS} = V_x$$

Given:

$$V_{O,SAT} = V_{OS} - V_{DD} = 0.5$$

$$= V_{OS} - (V_{GS} - V_{TH})$$

$$V_{GS} - V_{TH} = 0.3$$

$$\therefore 0.5 = V_{OS} - 0.3$$

$$\therefore V_{OS} = 0.8$$

$$V_D = 0.8$$

$$\therefore V_S = 0$$

$$\therefore \boxed{V_y = 0.8}$$

$$V_{R2} = V_{DD} - V_y$$

$$= 3 - 0.8$$

$$= 2.2V$$

3(w) (continued)

$$V_{R2} = 2.2V$$

$$\therefore I_x = \frac{2.2}{10000}$$

$$I_x = 0.22 \text{ mA}$$

Solve for  $V_x$ 

$$V_{GS} - V_{TH,N} = 0.3$$

$$V_x - V_{TH,N} = 0.3$$

$$V_x - 0.5 = 0.3$$

$$\therefore V_x = 0.8 \text{ V}$$

Solve for  $(W/L)$ 

$$I_{x1} = \frac{1}{2} k_{P,n} \left(\frac{W}{L}\right) (V_{GS})^2$$

$$\frac{2.2 \times 10^{-3} (2)}{(100 \times 10^{-6}) (0.3^2)} = \frac{W}{L}$$

$$\therefore \frac{W}{L} = 48.89$$

Sanity Check:

$$V_{GS} > V_{TH}$$

$$0.8 > 0.5$$

 $\therefore M_1 \text{ is ON } \checkmark$ 

$$V_{GS} > V_{DD}$$

$$0.8 > 0.3$$

 $\therefore M_1 \text{ is SAT } \checkmark$ 

$$\text{KVL Right Side: } 3V - (10k)(0.22 \times 10^{-3}) - V_y = 0$$

$$3V - 2.2 - 0.8 = 0$$

$$0 = 0 \quad \checkmark$$

KVL Left Side:

$$V_x + V_{R1} - V_{R2} - V_y = 0$$

$$0.8 + 2.2 - 2.2 - 0.8 = 0$$

$$0 = 0 \quad \checkmark$$

Solve for  $R_x$ 

$$I_1 = \frac{3 - V_x}{10k}$$

$$= \frac{3 - 0.8}{10k}$$

$$= 0.22 \text{ mA}$$

$$\therefore R_x = \frac{V_x}{I_1}$$

$$= \frac{0.8 \text{ V}}{0.22 \times 10^{-3} \text{ A}}$$

$$\therefore R_x = 3636.36 \Omega$$

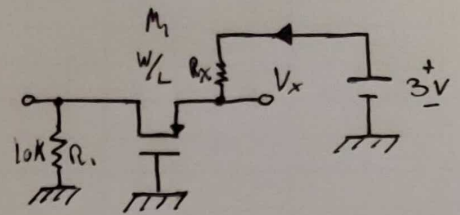
Tristan Denning

Problem 3(b)

1-1W # 05

**3(b)**

Situation: Find the unknown parameters ( $V_x$ ,  $I_x$ ,  $V_y$ ,  $W/L$ ) of the following circuit. Use  $V_{DD} = 0.8V$ , and  $V_{D,SAT} = 0.5$ .

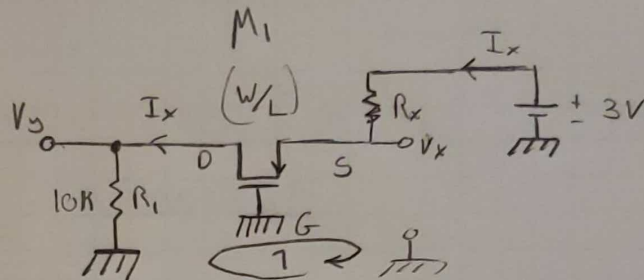


Goal: (See 3(a.))

Plan: (See 3(a.))

Solution:

Redraw



Observe:

$$\begin{aligned} V_G &= 0 \\ V_D &= V_y \\ V_x &= V_S \end{aligned}$$

Given:

$$\begin{aligned} V_{DD} &= 0.8V \\ &= (V_{SG} - |V_{TH,P}|) \end{aligned}$$

$$0.8 = V_{SG} - 0.4$$

$$\therefore V_{SG} = 1.2V$$

$$V_G = 0, V_S = 1.2V$$

$$\therefore V_S = \boxed{V_x = 1.2V}$$

$$\therefore V_{TH,P} = -0.4V$$

Given:

$$V_{D,SAT} = V_{SD} - V_{DD}$$

$$0.5 = V_{SD} - 0.8$$

$$\therefore V_{SD} = 1.3V$$

KVL (1):

$$V_y + V_{SD} - V_x = 0$$

$$V_y + 1.3 - 1.2 = 0$$

$$\therefore \boxed{V_y = -0.1V}$$



**3(b)** (Continued)

$$V_G = -1V$$

$$\therefore I_x = \frac{V_G}{R_1} = \frac{-1}{10000}$$

$$\boxed{I_x = -100 \mu A}$$

$$I_x = -100 \times 10^{-6} = \frac{1}{2} k_P \left(\frac{W}{L}\right)_P (V_{GD})^2$$

$$\frac{W}{L} = \frac{-2(100 \times 10^{-6})}{(50 \times 10^{-6})(0.8^2)}$$

$$\therefore \boxed{\frac{W}{L} = -6.25}$$

### Sanity Check

The result for  $\frac{W}{L}$  is somewhat insane, since negative width and length are not feasible quantities.

This could be a result of:

1.) I Misunderstand Simple Algebra and the following argument is incorrect:

$$V_{DD} = 0.8V = (V_{SG} - |V_{THP}|) \quad \therefore \text{Given}$$

$$\therefore V_{SG} = 1.2V \quad \therefore V_{THP} = -0.4V$$

$$\Rightarrow V_{D,SAT} = 0.5 = V_{SD} - V_{DD}$$

$$\therefore V_{SD} = 1.3V$$

$$\therefore V_{DD} = 0.8V$$

$$\therefore \frac{V_G + V_{SD}}{V_G} = \frac{V_{SG}}{V_G} = \frac{1.2 - 1.3}{-1} = \boxed{-0.1V} \quad \therefore \text{KVL}$$

or 2.) The Given parameters are not the appropriate quantities for the given PMOS Configuration

or 3.) Some Sign Convention I Overlooked